Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	406	438/140.ccls. and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:04
L3	18	438/140.ccor. and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:04
L4	702	438/203,259,286,335.ccls. and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:30
L5	539	257/335.ccls. and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:30
L6	87	257/335.ccor. and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:33
L7	82	257/339,340.ccor. and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:37
L8	66	257/409.ccor. and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:37
S1	1	@pn="6706567"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 10:58

S2	1	@pn="6258674"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 09:09
S3	1	@pn="5869875"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 09:42
S5	1	@pn="5640034"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 09:54
S6	0	@ad<"20000728" and source same trench same (high adj density adj diffusion) same electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 09:57
S7	586	@ad<"20000728" and source same trench same diffusion same electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 09:58
S8	248	@ad<"20000728" and source same trench same diffusion adj layer same electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 10:12
S9	31	@ad<"20000728" and source same trench same diffusion adj layer same source adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 10:24
S10	5	@ad<"20000728" and source same trench same (polysilicon (polycrystalline adj silicon)) same diffusion adj layer same source adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 10:37

S11	1	@ad<"20000728" and source same trench same (polysilicon (polycrystalline adj silicon)) same n+ adj layer same source adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 11:37
S12	1701	@ad<"20000728" and high adj voltage adj device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 11:41
S14	686	S12 and ("438"/$.ccls. or "257"/$.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 11:38
S15	1	S14 and source near3 trench near3 polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 11:40
S16	18	DMOS and source near3 trench near3 polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 12:03
S17	5	@ad<"20000728" and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 11:41
S18	19	DMOS and source near8 trench near8 polysilicon and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 12:04
S19	14	S18 not S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 12:04